TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# 2SK2035

High Speed Switching Applications Analog Switching Applications

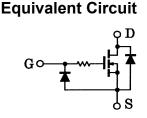
- High input impedance.
- Low gate threshold voltage:  $V_{th} = 0.5 \sim 1.5 \text{ V}$
- Excellent switching times:  $t_{on} = 0.16 \ \mu s \ (typ.)$

 $t_{off} = 0.15 \ \mu s \ (typ.)$ 

- Small package
- Enhancement-mode

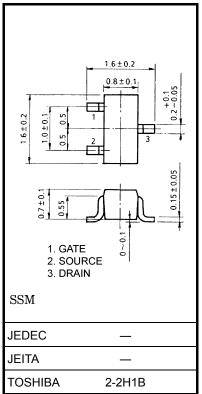
#### Marking





## Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V <sub>DS</sub>	20	V
Gate-source voltage	V <sub>GSS</sub>	10	V
Drain current	۱ <sub>D</sub>	100	mA
Drain power dissipation	PD	100	mW
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C



Weight: 2.4 mg (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

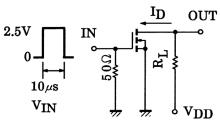
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

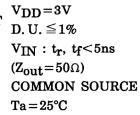
Note: This transistor is electrostatic sensitive device. Please handle with caushon.

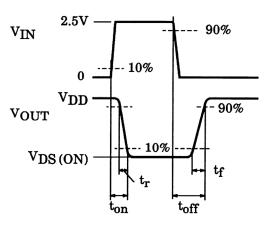
**Electrical Characteristics (Ta = 25°C)** 

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = 10 \text{ V}, \text{ V}_{DS} = 0$	_		1	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = 100 \ \mu A, \ V_{GS} = 0$	20	_	_	V
Drain cut-off curre	ent	I <sub>DSS</sub>	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0$	_	_	1	μA
Gate threshold vo	Itage	V <sub>th</sub>	$V_{DS} = 3 \text{ V}, \text{ I}_{D} = 0.1 \text{ mA}$	0.5	_	1.5	V
Forward transfer a	admittance	Y <sub>fs</sub>	$V_{DS} = 3 \text{ V}, \text{ I}_{D} = 10 \text{ mA}$	25	50	_	mS
Drain-source ON resistance		R <sub>DS (ON)</sub>	$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$	_	8	12	Ω
Input capacitance		C <sub>iss</sub>	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	8.5	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	3.3	_	pF
Output capacitance		C <sub>oss</sub>	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	9.3	_	pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = 3 \text{ V}, \text{ I}_{D} = 10 \text{ mA}, \text{ V}_{GS} = 0 \text{~} 2.5 \text{ V}$	_	0.16	_	μs
	Turn-off time	t <sub>off</sub>	$V_{DD}$ = 3 V, $I_{D}$ = 10 mA, $V_{GS}$ = 0~2.5 V	_	0.15	_	

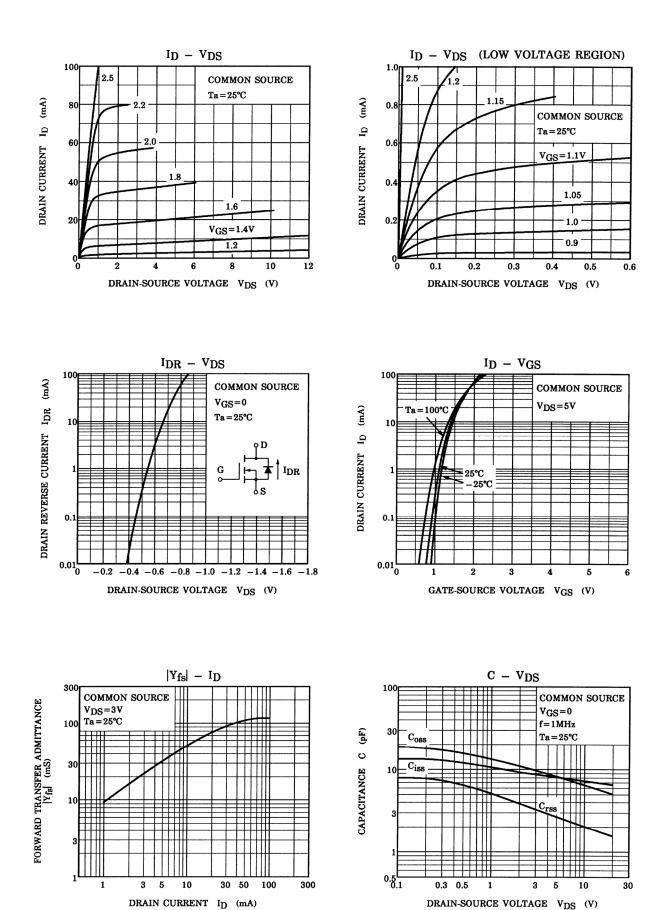
## Switching Time Test Circuit



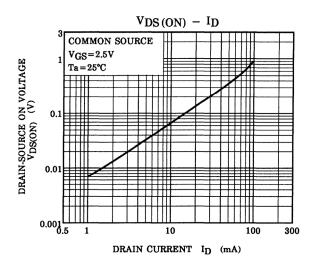


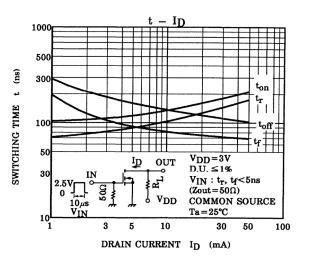


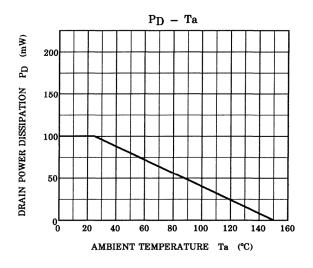
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